Name: Qualfication Report TP65H050G4BS Version: 1.00

Document Number: D-01675 Published: 09-Jul-2021 12:07

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Product Qualification Report

1. Purpose

 The purpose of this specification is to document the Qualification Report for TP65H050G4BS

2. Scope

- a. The products listed in section 1 are fully qualified and released to production as commercial grade products.
- Qualification test results on these products may reference existing qualification results of similar products per the use of generic data as defined in section 2.2 of AEC-Q101 Rev D1
- c. Each of the referenced part numbers share the same major assembly process and material elements as defined in Stress Test qualification for Automotive Grade Semiconductors, AEC-Q101 and are considered to be part of the same qualification family.

3. Qualification Process

- a. All Fab Lots were processed separately with a discrete amount of time between lots. All lots were assembled using the same Assembly House, on the same assembly line. All lots undergo Final Test using the documented test flow and are screened against documented test limits as appropriate to their part number. All processes and test conditions are documented and maintained under revision control as part of the Transphorm Quality Management System.
- b. Documented process and test conditions that are used for qualification of products are designated "Process of Record". Changes to the Process of Record are managed through the Process/Product Change Notification Procedure, which is part of the Transphorm Quality Management System.
- 4. ESD Results: 3 parts pass for each test
 - a. Standard Used: ANSI/ESDA/JEDEC JS-002-2018
 - b. HBM (Human Body Model): ±700V
 - c. CDM (Charge Device Model): ±2000V

5. Mechanical Tests: All tests passed

Test Name	Reference Standard
Solderability	JESD22 A113
Bond Pull Strength	MIL STD-833 M2011
Bond Shear	JESD22-B116

Reliability Testing

a. Failed devices are analyzed for root cause and correction. Only a representative sample needs to be analyzed, though some level of analysis will be applied to every failed part. Acceptable root cause and corrective action and successful demonstration of corrective and preventative actions will constitute successful qualification of a device. The part and/or qualification family can be qualified as long as containment of any problems are demonstrated until corrective and/or preventative actions are in place.

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7. Electrical Test Parameters

a. Components submitted for qualification testing must meet all datasheet parameters before and after stress testing

Parameter	Symbol	Conditions	LSL	USL	Unit
Drain to source leakage current	IDSS	V _{DS} = 650V V _{GS} = 0V T _J =25°C		40	μΑ
Gate to Source Forward Leakage Current	Igss	V _{GS} =20V		100	nA
Drain source on resistance	R _{DS}	V _{GS} = 8V I _D =5A T _J = 25°C		60	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ID=0.5mA	3.3	4.8	V

8. Reliability Qualification Test Results

TEST	SYMBOL	CONDITIONS	SAMPLE	RESULT
Moisture/Reflow	MSL-3	MSL-3	9 lots	0 Fails
Sensitivity	moz o	Pb-free	25 units per lot	PASS
Constitutiy		T _C = 260°C	225 total parts	17.00
		10= 200 0	220 total parts	
High Temperature	HTRB	T _J =150°C	3 lots	0 Fails
Reverse Bias		$V_{DS} = 520V$	77 parts per lot	PASS
		1000 HRS	231 total parts	
Highly Accelerated	HAST	130°C,85% RH	3 lots	0 Fails
Temp and Humidity	14.0	33.3 PSI	77 parts per lot	PASS
Test		Bias = 100V	231 total parts	
		96 HRS		
	Ť	MSL pre-con		
Temperature Cycle	TC	-55°C / 150°C	3 lots	0 Fails
		2 Cycles / HR	77 parts per lot	PASS
		500 Cycles	231 total parts	
		MSL pre-con		
Power Cycle	PC	25°C / 125°C	3 lots	0 Fails
		$\Delta T = 100^{\circ}C$	77 parts per lot	PASS
		7500 Cycles	231 total parts	
High Temperature	HTGB	150°C	3 lots	0 Fails
Gate bias		1000 HRS	77 parts per lot	PASS
		V _{GSS} =18V	231 total parts	

9. Referenced Documents

- a. AEC-Q101: Stress Test Qualification for Automotive Grade Discrete Semiconductors
- b. JESD47: Stress-Test Driven Qualification of Integrated Circuits
- c. MIL-PRF-38535: Performance specification-Integrated Circuits Manufacturing General Specification for Department of Defense

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- d. JESD22-A108C: High Temperature Reverse Bias (HTRB)
- e. JESD22-A110D: Highly Accelerated Temperature and Humidity Stress Test (HAST)
- f. JESD22-A104D: Temperature Cycle (TC)

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g. JESD22-A122: Power Cycle (PC)

h. JS-001-2012: Electrostatic Discharge Human Body Model i. J-STD-020D.1: Moisture/Reflow Sensitivity Classification

j. JESD22-A102: Pre-conditioning k. M2011: Wirebond strength I. JESD22-B116: Bond Shear

10. Signature Approval

Ronald Barr **VP Quality** April 27, 2020

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